

Silicon N-Channel Power MOSFET

Description

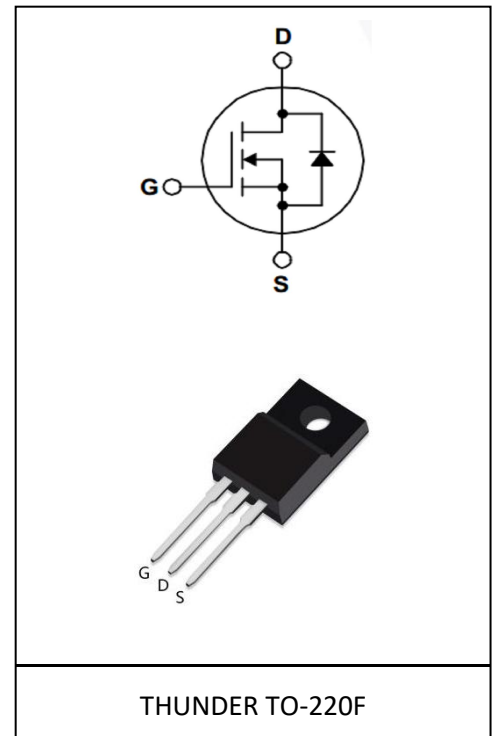
The TH10N65PF uses advanced technology and design to provide excellent $R_{DS(ON)}$. It can be used in a wide variety of applications.

General Features

- $V_{DS}=650V, I_D=10A$
- Low ON Resistance
- Low Reverse transfer capacitances
- 100% Single Pulse avalanche energy Test

Application

- Power switching application
- Adapter and charger



Electrical Characteristics @ $T_a=25^\circ\text{C}$ (unless otherwise specified)

a) Absolute Maximum Ratings:

Symbol	Parameter	Value	Units
V_{DS}	Drain-to-Source Breakdown Voltage	650	V
I_D	Drain Current (continuous) at $T_c=25^\circ\text{C}$	10	A
I_{DM}	Drain Current (pulsed)	40	A
V_{GS}	Gate to Source Voltage	+/-30	V
P_{tot}	Total Dissipation at $T_c=25^\circ\text{C}$	70	W
T_j	Max. Operating Junction Temperature	150	$^\circ\text{C}$
E_{AS}	Single Pulse Avalanche Energy	500	mJ

b) Electrical Parameters:

Symbol	Parameter	Test Conditions	Min	Typ	Max	Unit
V_{DS}	Drain-source Voltage	$V_{GS}=0V, I_D=250\mu A$	650			V
$R_{DS(on)}$	Static Drain-to-Source on-Resistance	$V_{GS}=10V, I_D=5A$		0.8	1.0	Ω
$V_{GS(th)}$	Gated Threshold Voltage	$V_{DS}=V_{GS}, I_D=250\mu A$	2.0	2.8	4.0	V
I_{DSS}	Drain to Source leakage Current	$V_{DS}=650V, V_{GS}=0V$			1.0	μA
$I_{GSS(F)}$	Gated to Source Foward Leakage	$V_{GS}=+30V$			100	nA
$I_{GSS(R)}$	Gated to Source Reverse Leakage	$V_{GS}=-30V$			-100	nA
C_{iss}	Input Capacitance	$V_{GS}=0V,$ $V_{DS}=25V,$ $f=1.0MHZ$		1642		pF
C_{oss}	Output Capacitance			128		pF
C_{rss}	Reverse Transfer Capacitance			7		pF

c) Switching Characteristics

Symbol	Parameter	Test Conditions	Min	Typ	Max	Unit
$t_{d(on)}$	Turn-on Delay Time	$V_{DD}=325V, I_D=10A,$ $R_G=10\Omega$		27		nS
t_r	Turn-on Rise Time			22		nS
$t_{d(off)}$	Turn-off Delay Time			53		nS
t_f	Turn-off Fall Time			24		nS
Q_g	Total Gate Charge	$V_{DS}=520V$ $I_D=10A$ $V_{GS}=10V$		32		nC
Q_{gs}	Gate-Source Charge			8		nC
Q_{gd}	Gate-Drain Charge			12		nC

d) Source-Drain Diode Characteristics

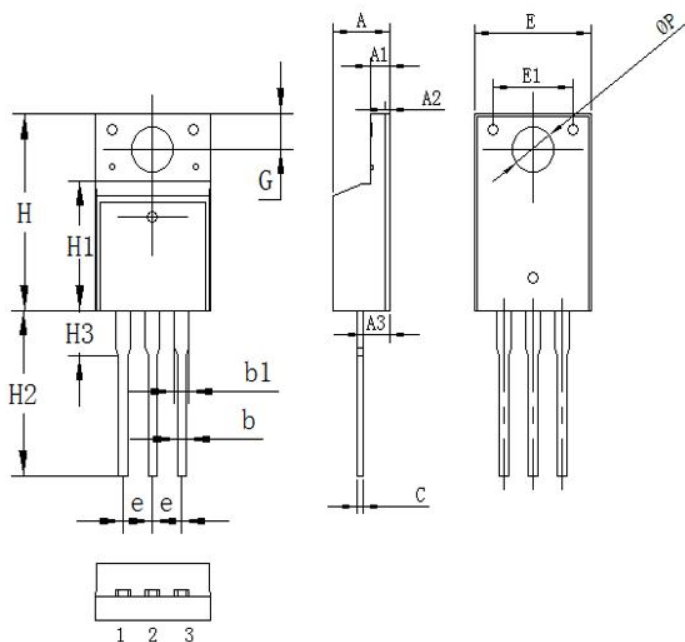
Symbol	Parameter	Test Conditions	Min	Typ	Max	Unit
I _{SD}	S-D Current(Body Diode)				10	A
I _{SDM}	Pulsed S-D Current(Body Diode)				40	A
V _{SD}	Diode Forward Voltage	V _{GS} =0V, I _{DS} =10A			1.4	v
t _{rr}	Reverse Recovery Time	T _J =25℃, I _F =10A di/dt=100A/us		528		nS
Q _{rr}	Reverse Recovery Charge			3220		μC
	*Pulse Test: Pulse Width <= 300μs, Duty Cycle< =2%					

Symbol	Parameter	Typ	Units
$R_{\theta JC}$	Junction-to-Case	2.14	$^\circ C/W$

Package Information

TO-220F PACKAGE

基本尺寸



Symbol	单位 mm		
	Min	Nom	Max
A	4.55	4.75	4.95
A1	2.40	2.60	2.80
A2	0.40	0.60	0.80
A3	2.10	2.30	2.50
b1	1.10	1.30	1.50
b	0.60	0.80	1.00
c	0.42	0.50	0.58
e	2.30	2.50	2.70
E	9.9	10.1	10.3
E1	6.8	7	7.2
H	15.8	16.0	16.2
H1	9.10	9.30	9.50
H2	12.5	13.0	13.5
H3	3.10	3.30	3.50
G	3.00	3.20	3.40
ΦP	3.00	3.20	3.40

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-Headquarters

WuXi Thunder Microelectronics Incorporated Limited

Building E1-9L, No.200 LingHu Road, XinWu district,WuXi,China 214135

Tel:+86-510-85160109

Fax:+86-510-85160109